### MDD172-16N1

## **Standard Rectifier Module**

$V_{\text{RRM}}$	<b>= 2</b> 2	x 1600 V
I <sub>fav</sub>	=	190 A
V <sub>F</sub>	=	0.96 V

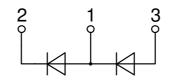
Phase leg

Part number

MDD172-16N1



Backside: isolated **E**72873



### Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- · Very low leakage current

### **Applications:**

- Diode for main rectification
- For single and three phase
- bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- · Field supply for DC motors

#### Package: Y4

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

#### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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## MDD172-16N1

Rectifier	ectifier			Rating	S		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			1700	V
V <sub>RRM</sub>	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1600	V
I <sub>R</sub>	reverse current	$V_{R} = 1600 V$	$T_{VJ} = 25^{\circ}C$			1	mA
		$V_{R} = 1600 V$	$T_{VJ} = 150^{\circ}C$			20	mA
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 150 A	$T_{VJ} = 25^{\circ}C$			1.07	V
		I <sub>F</sub> = 300 A				1.22	V
		$I_{F} = 150 \text{ A}$	T <sub>vJ</sub> = 125°C			0.96	V
		$I_{F} = 300 \text{ A}$				1.16	V
FAV	average forward current	$T_c = 100^{\circ}C$	T <sub>vJ</sub> = 150°C			190	A
I F(RMS)	RMS forward current	180° sine				300	Α
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 150°C			0.80	V
r <sub>F</sub>	slope resistance } for power	loss calculation only				0.8	mΩ
<b>R</b> <sub>thJC</sub>	thermal resistance junction to ca	ase				0.21	K/W
R <sub>thCH</sub>	thermal resistance case to heats	sink			0.08		K/W
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$			600	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			6.60	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			7.13	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}C$			5.61	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			6.06	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			217.8	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			211.5	kA²s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			157.4	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			152.8	kA²s
CJ	junction capacitance	V <sub>R</sub> = 400 V; f = 1 MHz	$T_{VJ} = 25^{\circ}C$		238		pF

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## MDD172-16N1

Package Y4				Ratings		S		
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					300	Α
T <sub>vj</sub>	virtual junction temperature				-40		150	°C
T <sub>op</sub>	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		125	°C
Weight						150		g
M <sub>D</sub>	mounting torque				2.25		2.75	Nm
M <sub>T</sub>	terminal torque				4.5		5.5	Nm
d <sub>Spp/App</sub>	creenage distance on surfa	ce   striking distance through air	terminal to terminal	14.0	10.0			mm
<b>d</b> <sub>Spb/Apb</sub>	creepage ustance on suna	ce   striking distance through an	terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second	50/60 Hz, RMS; liso⊾ ≤ 1 mA		3600			V
		t = 1 minute			3000			V

<u> </u>			
Date Code (DC)	DIXYS <b>N</b> yywwAA Part Number Lot.No: xxxxxx	Circuit	

Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

[	Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	MDD172-16N1	MDD172-16N1	Box	6	429724

Equiv	alent Circuits for	Simulation	* on die level	T <sub>vJ</sub> = 150 °C
	)- <u>R</u>	Rectifier		
$V_{0 max}$	threshold voltage	0.8		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	0.4		mΩ

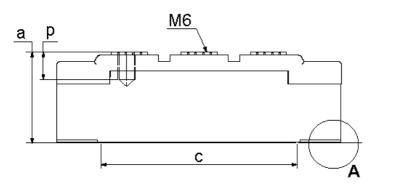
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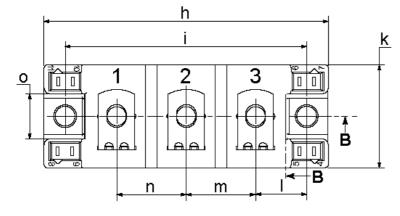
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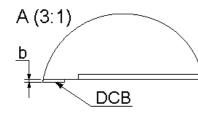
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Outlines Y4

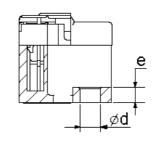


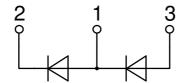


Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
а	30.0	30.6	1.181	1.205
b	typ.	0.25	typ. (	0.010
с	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
е	4.9	5.1	0.193	0.201
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
k	33.4	34.0	1.315	1.339
I	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
0	14.0	15.0	0.551	0.591
р	typ.	10.5	typ. 0.413	



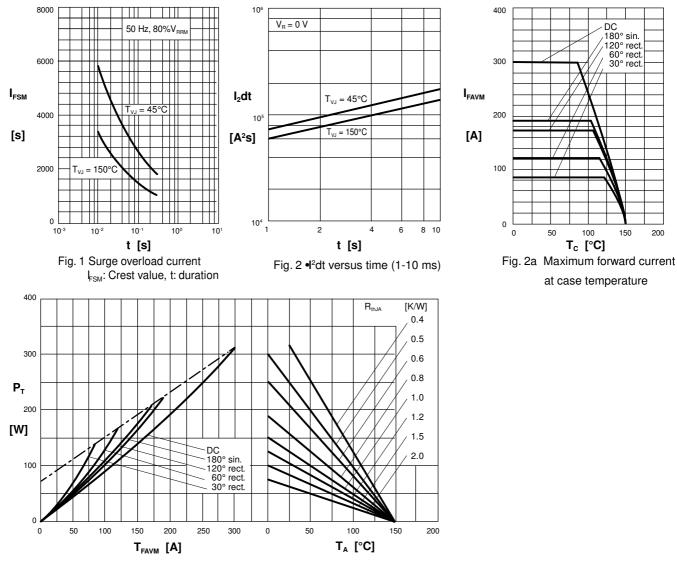




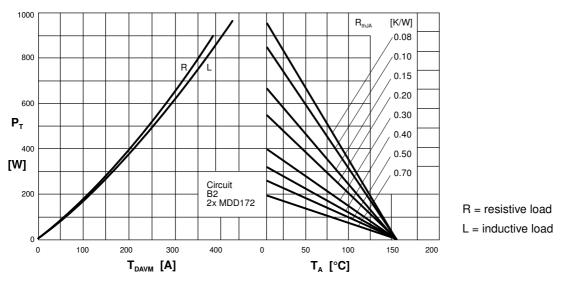


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### Rectifier







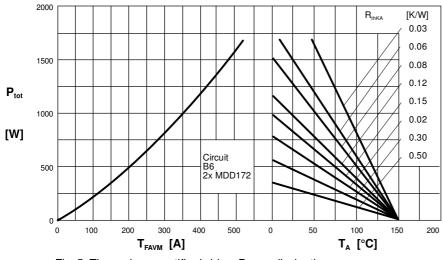


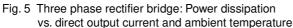


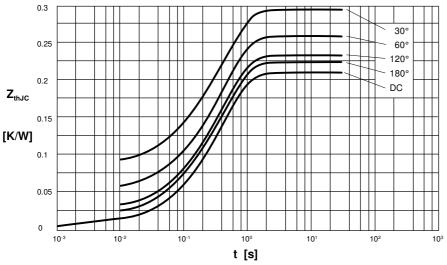
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### Rectifier



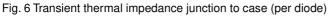


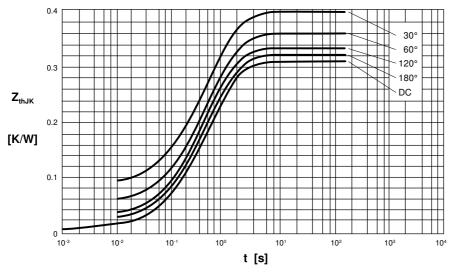


R<sub>thJC</sub> for various conduction angles d:

Constants for  $Z_{thJC}$  calculation:

i	<b>R</b> <sub>thi</sub> [K/W]	t <sub>i</sub> [s]
1	0.0087	0.001
2	0.0163	0.065
3	0.1850	0.400





 $R_{\mbox{\tiny thJK}}$  for various conduction angles d:

d	R <sub>thJK</sub> [K/W]
DC	0.310
180°	0.323
120°	0.333
60°	0.360
30°	0.395

Constants for  $Z_{thJK}$  calculation:

i 1 2 3 4	<b>R</b> <sub>thi</sub> [K/W] 0.0087 0.0163 0.1850 0.1000	t <sub>i</sub> [s] 0.001 0.065 0.400 1.290
4	0.1000	1.290

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Fig. 7 Transient thermal impedance junction to heatsink (per diode)

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